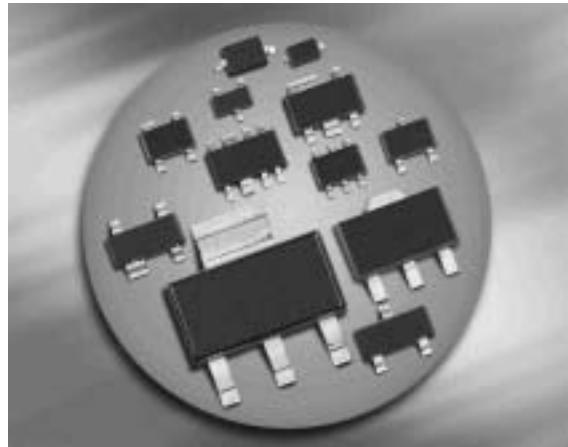


### PNP Silicon AF Transistor

- For general AF applications
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary type:  
BC817.../W, BC818.../W (NPN)
- Pb-free (RoHS compliant) package<sup>1)</sup>
- Qualified according AEC Q101



Type	Marking	Pin Configuration						Package
BC807-16	5As	1 = B	2 = E	3 = C	-	-	-	SOT23
BC807-16W	5As	1 = B	2 = E	3 = C	-	-	-	SOT323
BC807-25	5Bs	1 = B	2 = E	3 = C	-	-	-	SOT23
BC807-25W	5Bs	1 = B	2 = E	3 = C	-	-	-	SOT323
BC807-40	5Cs	1 = B	2 = E	3 = C	-	-	-	SOT23
BC807-40W	5Cs	1 = B	2 = E	3 = C	-	-	-	SOT323
BC808-25	5Fs	1 = B	2 = E	3 = C	-	-	-	SOT23
BC808-25W	5Fs	1 = B	2 = E	3 = C	-	-	-	SOT323
BC808-40	5Gs	1 = B	2 = E	3 = C	-	-	-	SOT23
BC808-40W	5Gs	1 = B	2 = E	3 = C	-	-	-	SOT323

<sup>1</sup>Pb-containing package may be available upon special request

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage BC807...	$V_{CEO}$	45	V
BC808...		25	
Collector-base voltage BC807...	$V_{CBO}$	50	
BC808...		30	
Emitter-base voltage	$V_{EBO}$	5	
Collector current	$I_C$	500	mA
Peak collector current	$I_{CM}$	1000	
Base current	$I_B$	100	
Peak base current	$I_{BM}$	200	
Total power dissipation- $T_S \leq 79 \text{ }^\circ\text{C}$ BC807, BC808	$P_{tot}$	330	mW
$T_S \leq 130 \text{ }^\circ\text{C}$ BC807W, BC808W		250	
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup> BC807, BC808	$R_{thJS}$	$\leq 215$	K/W
BC807W, BC808W		$\leq 80$	

<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Collector-emitter breakdown voltage $I_C = 10 \text{ mA}, I_B = 0$ , BC807...	$V_{(\text{BR})\text{CEO}}$	45	-	-	V
$I_C = 10 \text{ mA}, I_B = 0$ , BC808...		25	-	-	
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$ , BC807...	$V_{(\text{BR})\text{CBO}}$	50	-	-	
$I_C = 10 \mu\text{A}, I_E = 0$ , BC808...		30	-	-	
Emitter-base breakdown voltage $I_E = 10 \mu\text{A}, I_C = 0$	$V_{(\text{BR})\text{EBO}}$	5	-	-	
Collector-base cutoff current $V_{CB} = 25 \text{ V}, I_E = 0$ $V_{CB} = 25 \text{ V}, I_E = 0, T_A = 150^\circ\text{C}$	$I_{\text{CBO}}$	-	-	0.1 50	$\mu\text{A}$
Emitter-base cutoff current $V_{EB} = 4 \text{ V}, I_C = 0$	$I_{\text{EBO}}$	-	-	100	nA
DC current gain <sup>1)</sup> $I_C = 100 \text{ mA}, V_{CE} = 1 \text{ V}, h_{FE}\text{-grp. 16}$ $I_C = 100 \text{ mA}, V_{CE} = 1 \text{ V}, h_{FE}\text{-grp. 25}$ $I_C = 100 \text{ mA}, V_{CE} = 1 \text{ V}, h_{FE}\text{ grp. 40}$ $I_C = 500 \text{ mA}, V_{CE} = 1 \text{ V}$	$h_{FE}$	100 160 250 40	160 250 350 -	250 400 630 -	-
Collector-emitter saturation voltage <sup>1)</sup> $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	$V_{\text{CEsat}}$	-	-	0.7	V
Base emitter saturation voltage <sup>1)</sup> $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	$V_{\text{BESat}}$	-	-	1.2	

<sup>1</sup>Pulse test:  $t < 300\mu\text{s}$ ;  $D < 2\%$

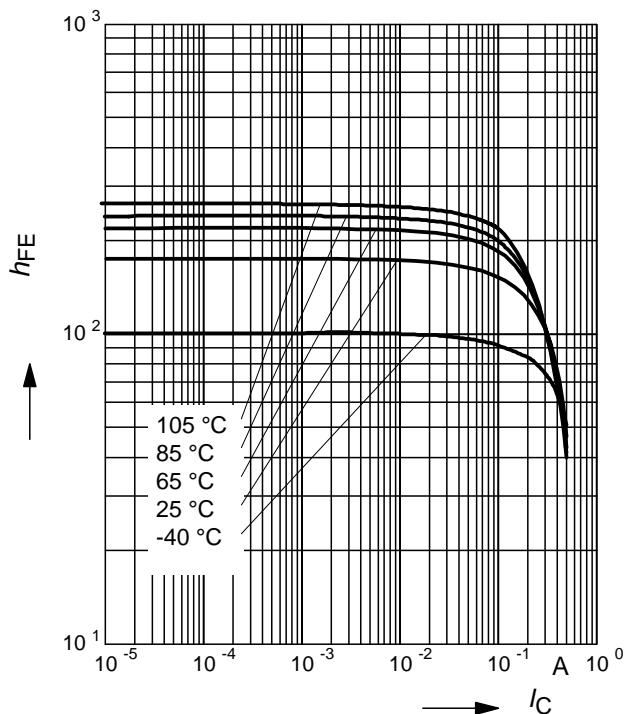
**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC Characteristics</b>					
Transition frequency $I_C = 50 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	$f_T$	-	200	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	$C_{cb}$	-	8	-	pF
Emitter-base capacitance $V_{EB} = 0.5 \text{ V}, f = 1 \text{ MHz}$	$C_{eb}$	-	60	-	

**DC current gain  $h_{FE} = f(I_C)$**

$V_{CE} = 1 \text{ V}$

$h_{FE}$ -grp. 16



**DC current gain  $h_{FE} = f(I_C)$**

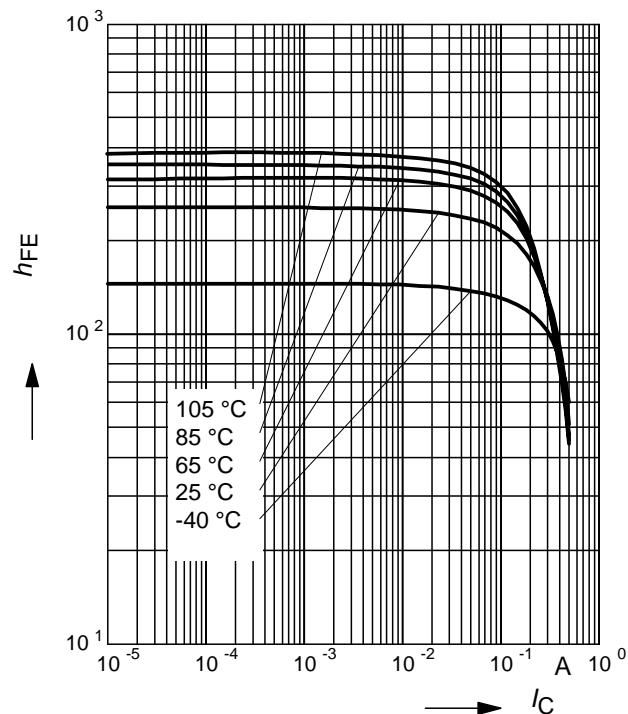
$V_{CE} = 1 \text{ V}$

$h_{FE}$ -grp. 25

**DC current gain  $h_{FE} = f(I_C)$**

$V_{CE} = 1 \text{ V}$

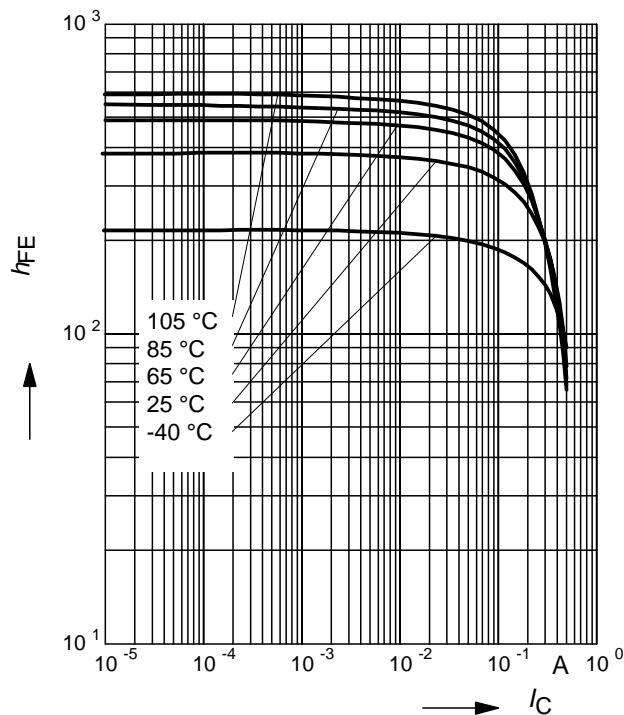
$h_{FE}$ -grp. 25



**DC current gain  $h_{FE} = f(I_C)$**

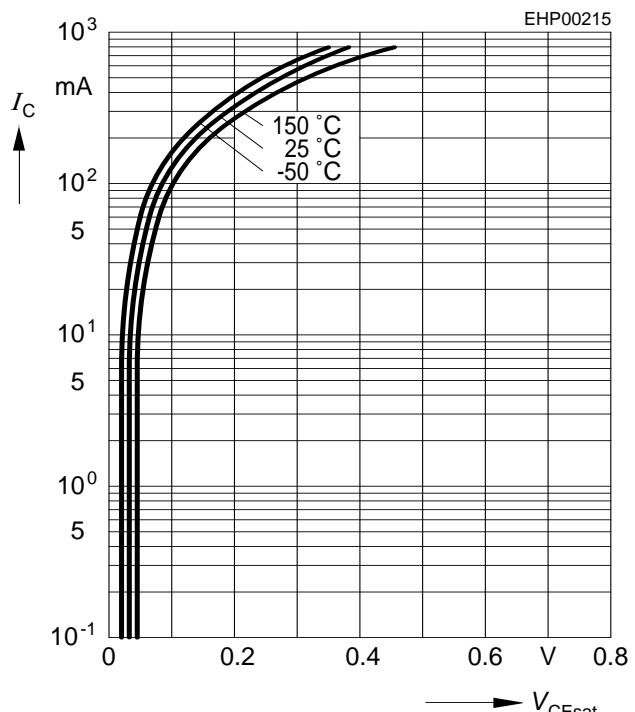
$V_{CE} = 1 \text{ V}$

$h_{FE}$ -grp. 40



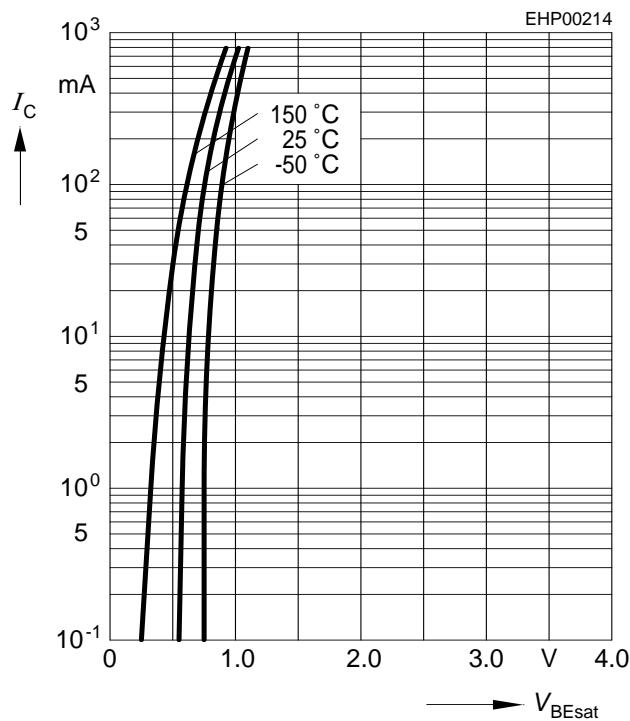
**Collector-emitter saturation voltage**

$I_C = f(V_{CEsat}), h_{FE} = 10$

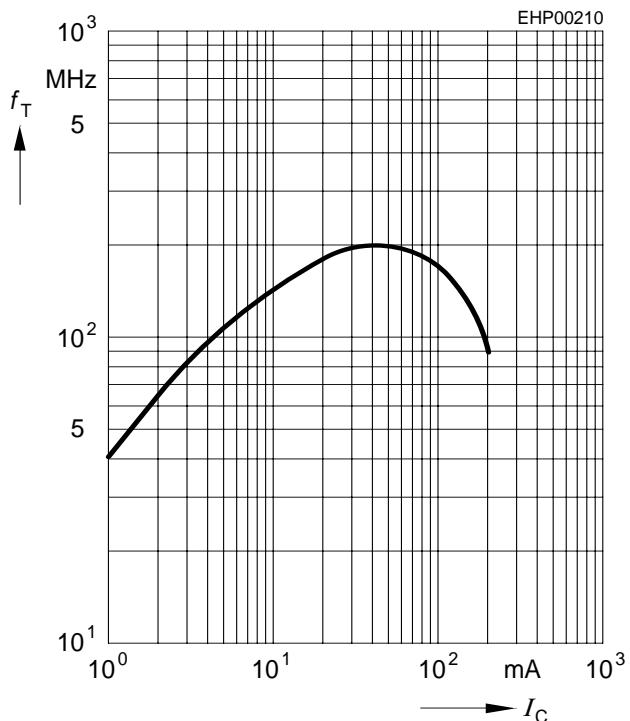


**Base-emitter saturation voltage**

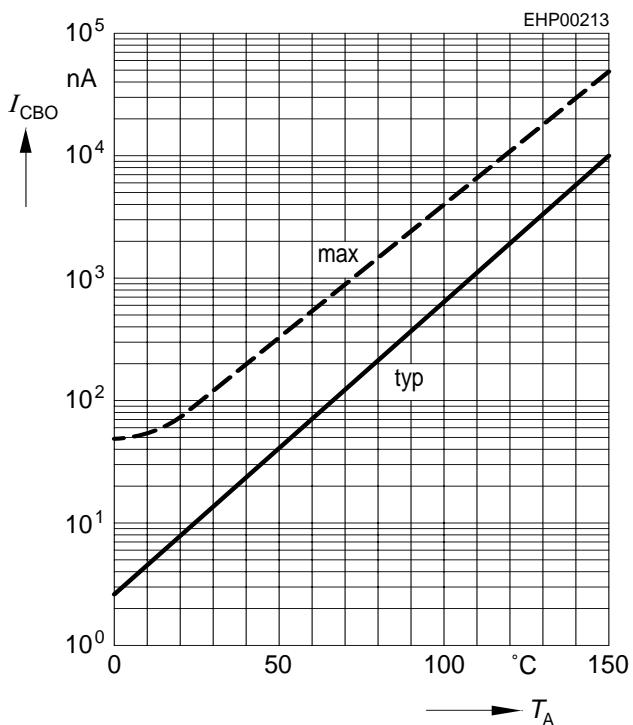
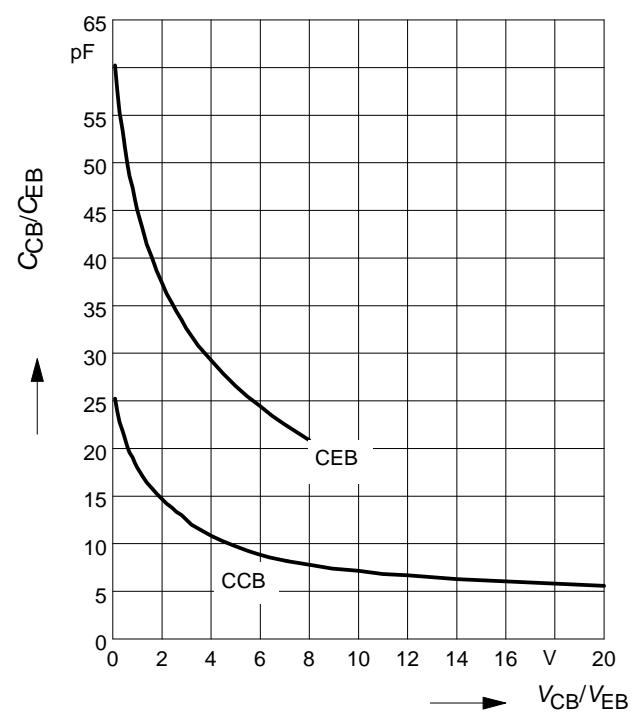
$$I_C = f(V_{BEsat}), h_{FE} = 10$$


**Transition frequency  $f_T = f(I_C)$** 

$V_{CE}$  = parameter in V,  $f = 2$  GHz

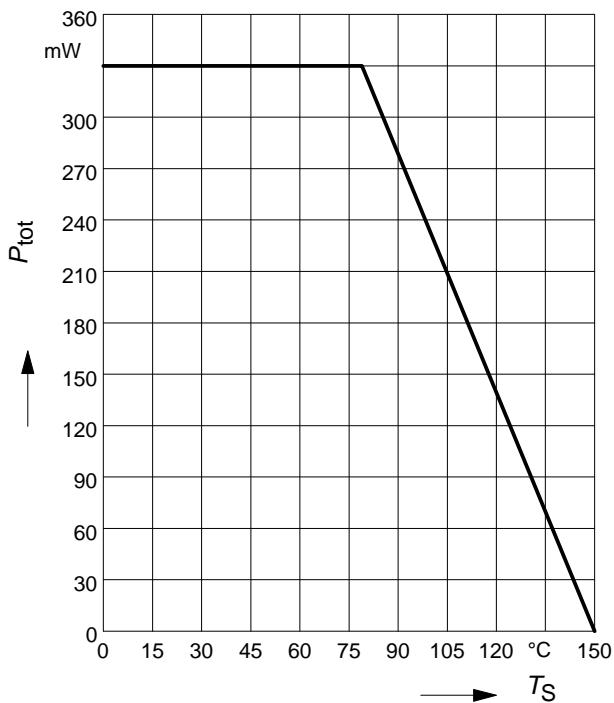

**Collector cutoff current  $I_{CBO} = f(T_A)$** 

$$V_{CBO} = 25 \text{ V}$$


**Collector-base capacitance  $C_{cb} = f(V_{CB})$** 
**Emitter-base capacitance  $C_{eb} = f(V_{EB})$** 


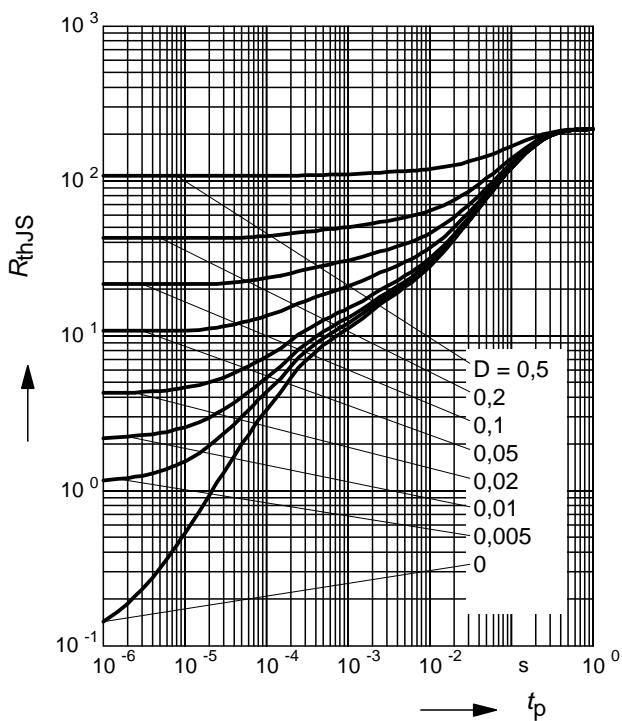
**Total power dissipation  $P_{\text{tot}} = f(T_S)$**

BC807, BC808



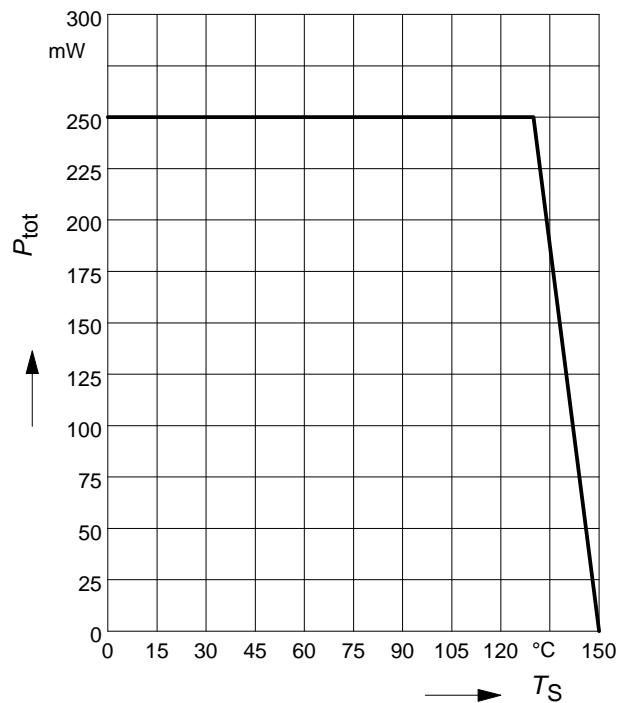
**Permissible Pulse Load  $R_{\text{thJS}} = f(t_p)$**

BC807, BC808



**Total power dissipation  $P_{\text{tot}} = f(T_S)$**

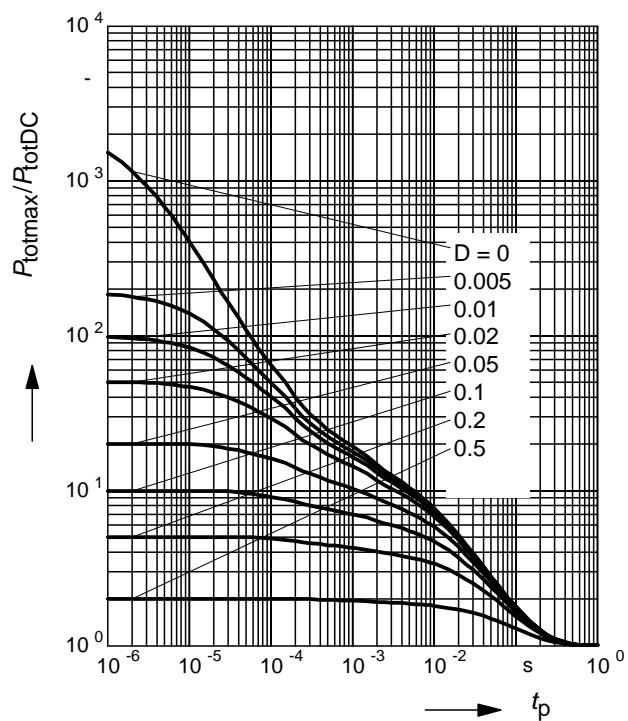
BC807W, BC808W



**Permissible Pulse Load**

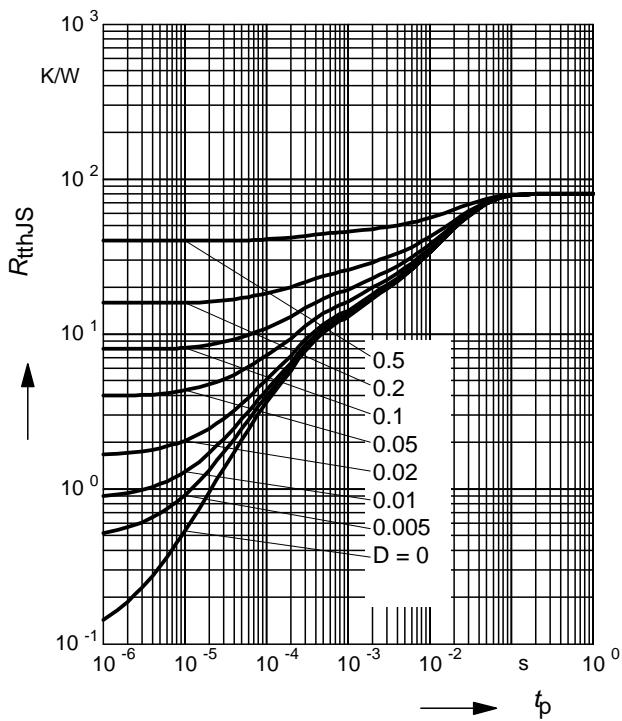
$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$

BC807, BC808



**Permissible Puls Load**  $R_{\text{thJS}} = f(t_p)$

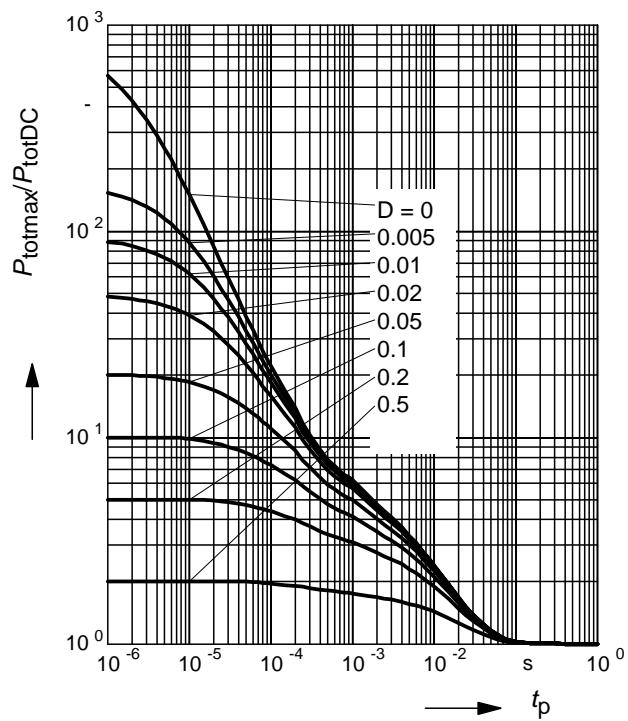
BC807W, BC808W



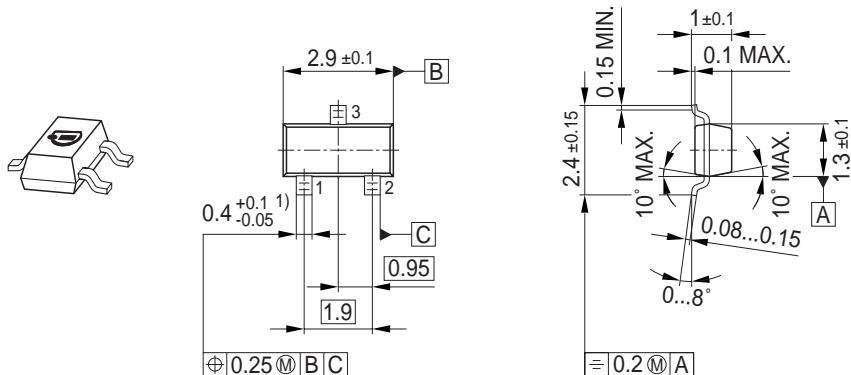
**Permissible Pulse Load**

$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$

BC807W, BC808W

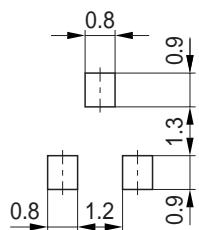


## Package Outline

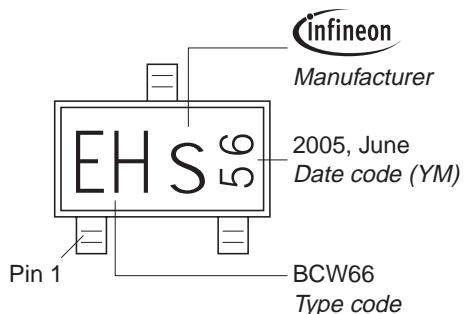


1) Lead width can be 0.6 max. in dambar area

## Foot Print

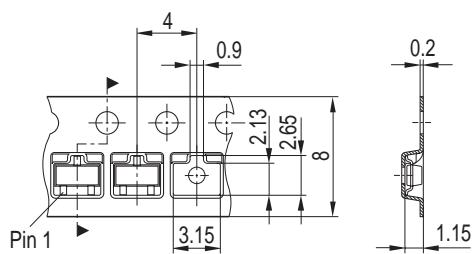


## Marking Layout (Example)

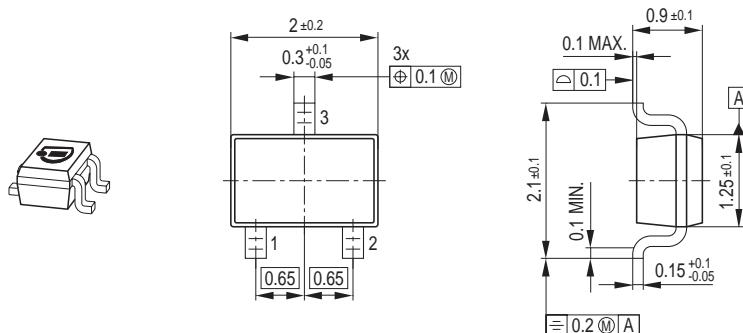


## Standard Packing

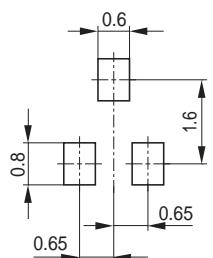
Reel ø180 mm = 3.000 Pieces/Reel  
Reel ø330 mm = 10.000 Pieces/Reel



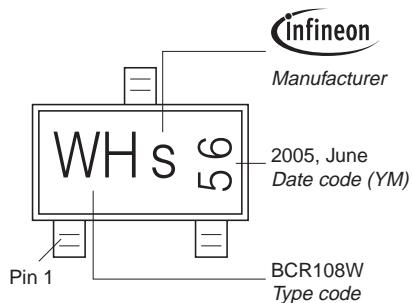
## Package Outline



## Foot Print

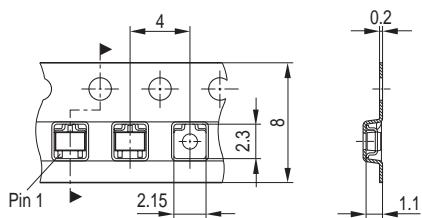


## Marking Layout (Example)



## Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel  
 Reel ø330 mm = 10.000 Pieces/Reel



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